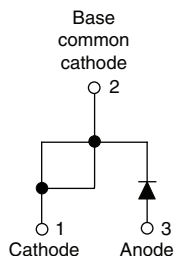


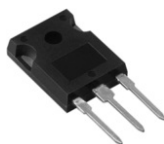
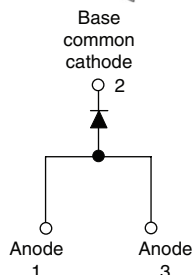
Ultrafast Soft Recovery Diode, 60 A FRED Pt™

60EPU02PbF



TO-247AC modified

60APU02PbF



TO-247AC

FEATURES

- Ultrafast recovery
- 175 °C operating junction temperature
- Lead (Pb)-free ("PbF" suffix)
- Designed and qualified for industrial level



RoHS*
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

PRODUCT SUMMARY

t_{rr}	35 ns
$I_{F(AV)}$	60 A
V_R	200 V

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		200	V
Continuous forward current	$I_{F(AV)}$	$T_C = 127\text{ °C}$	60	A
Single pulse forward current	I_{FSM}	$T_C = 25\text{ °C}$	800	
Maximum repetitive forward current	I_{FRM}	Square wave, 20 kHz	120	
Operating junction and storage temperatures	T_J, T_{Stg}		- 55 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_R	$I_R = 100\text{ }\mu\text{A}$	200	-	-	V
Forward voltage	V_F	$I_F = 60\text{ A}$	-	0.98	1.08	
		$I_F = 60\text{ A}, T_J = 175\text{ °C}$	-	0.81	0.88	
Reverse leakage current	I_R	$V_R = V_R\text{ rated}$	-	-	50	μA
		$T_J = 150\text{ °C}, V_R = V_R\text{ rated}$	-	-	2	mA
Junction capacitance	C_T	$V_R = 200\text{ V}$	-	87	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

* Pb containing terminations are not RoHS compliant, exemptions may apply

60EPU02PbF/60APU02PbF



Vishay High Power Products Ultrafast Soft Recovery Diode,
60 A FRED Pt™

DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t _{rr}	I _F = 1.0 A, dI _F /dt = 200 A/μs, V _R = 30 V		-	-	35	ns
		T _J = 25 °C	I _F = 60 A dI _F /dt = 200 A/μs V _R = 160 V	-	28	-	
		T _J = 125 °C		-	50	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	4	-	A
		T _J = 125 °C		-	8	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	59	-	nC
		T _J = 125 °C		-	220	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R_{thJC}		-	-	0.70	K/W
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	5.5	-	g
			-	0.2	-	oz.
Mounting torque			-	-	1.2	N · m
Marking device		Case style TO-247AC modified	60EPU02			
		Case style TO-247AC	60APU02			

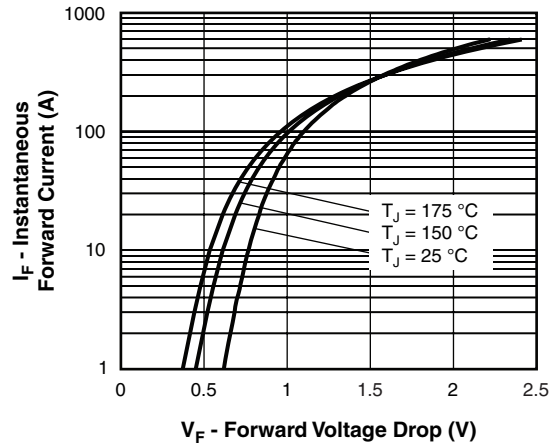


Fig. 1 - Typical Forward Voltage Drop Characteristics

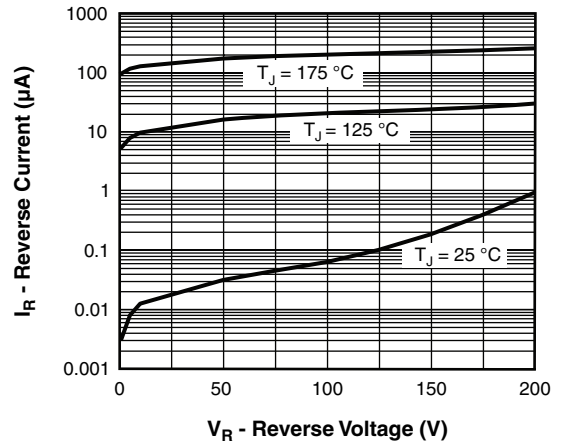


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

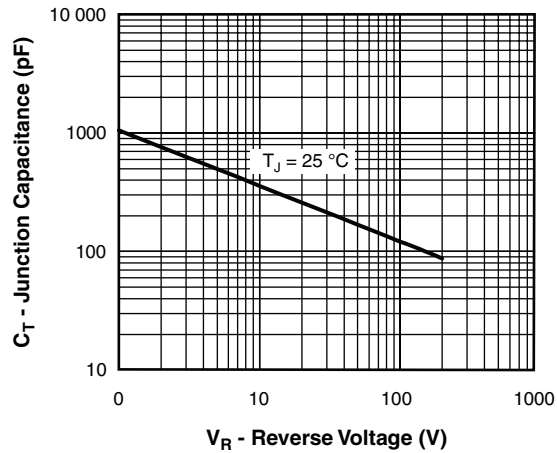


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

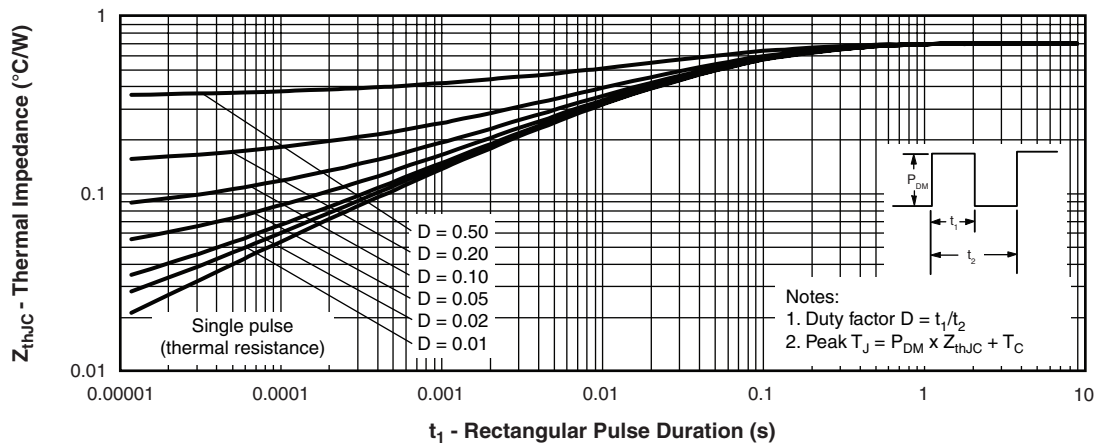


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

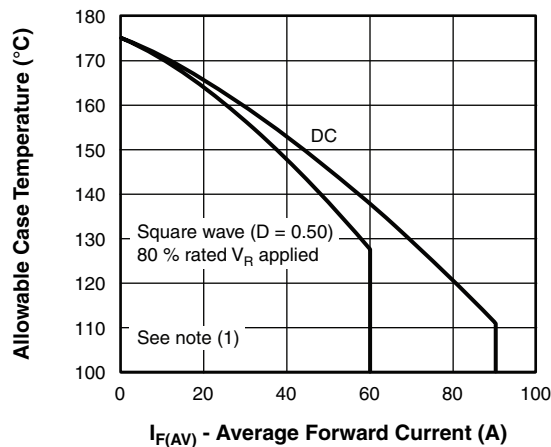


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

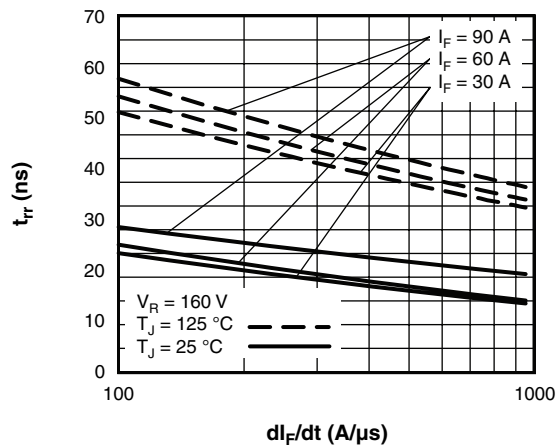


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

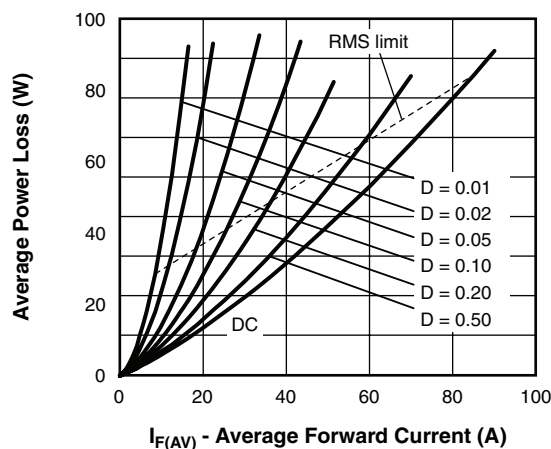


Fig. 6 - Forward Power Loss Characteristics

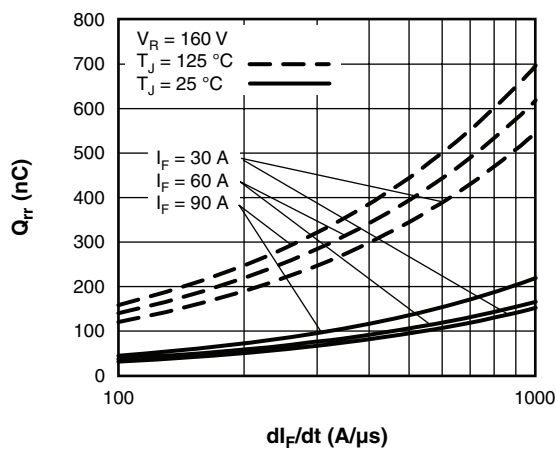


Fig. 8 - Typical Stored Charge vs. dI_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R

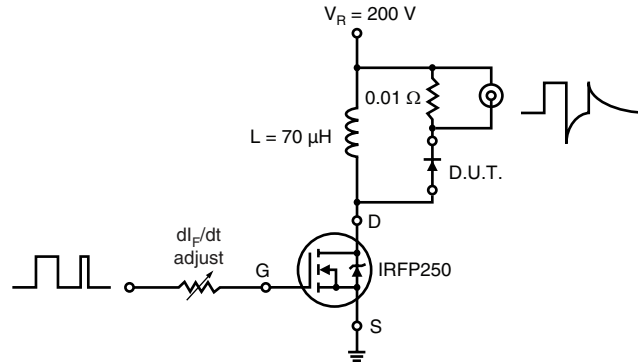


Fig. 9 - Reverse Recovery Parameter Test Circuit

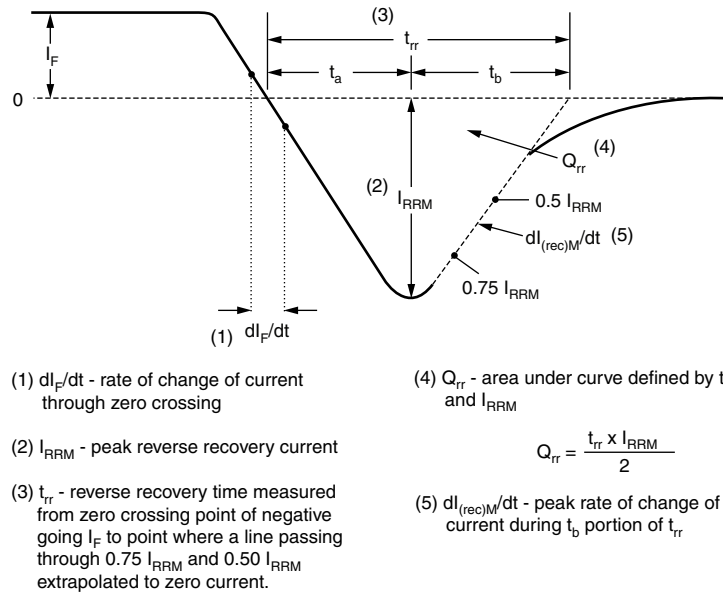


Fig. 10 - Reverse Recovery Waveform and Definitions

60EPU02PbF/60APU02PbF

Vishay High Power Products Ultrafast Soft Recovery Diode,
60 A FRED Pt™



ORDERING INFORMATION TABLE

Device code	60	E	P	U	02	PbF
	①	②	③	④	⑤	⑥
	1	-	-	-	-	-
	2	-	-	-	-	-
	3	-	-	-	-	-
	4	-	-	-	-	-
	5	-	-	-	-	-
	6	-	-	-	-	-

1 - Current rating (60 = 60 A)

2 - Circuit configuration:
E = Single diode
A = Single diode, 3 pins

3 - Package:
P = TO-247AC (modified)

4 - Type of silicon:
U = Ultrafast recovery

5 - Voltage rating (02 = 200 V)

6 - • None = Standard production
• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95001
Part marking information	http://www.vishay.com/doc?95006



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